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AMENDMENT TRANSMITTAL LETTER				Docket No. 8733.170.10-US	
Application No. 10/671,552-Conf. #4274		Filing Date September 29, 2003		Examiner A. G. Ghyka	
				Art Unit 2812	
Applicant(s): Kwang Nam Kim et al.					
Invention: METHOD OF FORMING SILICON OXIDE LAYER AND METHOD OF MANUFACTURING THIN FILM TRANSISTOR THEREBY					
TO THE COMMISSIONER FOR PATENTS					
Transmitted herewith is an amendment in the above-identified application.					
The fee has been calculated and is transmitted as shown below.					
CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	10	- 20 =		x	0.00
Independent Claims	1	- 3 =		x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity					
<input checked="" type="checkbox"/> No additional fee is required for this amendment.					
<input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of \$ _____. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Director is hereby authorized to charge and credit Deposit Account No. <u>50-0911</u> as described below. A duplicate copy of this sheet is enclosed.					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 Rebecca Goldman Rudich Attorney Reg. No.: 41,786				Dated: <u>July 9, 2004</u>	
MCKENNA LONG & ALDRIDGE LLP 1900 K Street, N.W. Washington, DC 20006 (202) 496-7463					



Docket No.: 8733.170.10-US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Kwang Nam KIM, et al.

Confirmation No. 4274

Application No.: 10/671,552

Art Unit: 2812

Filed: September 29, 2003

Examiner: Ghyka, Alexander G.

For: METHOD OF FORMING SILICON OXIDE
LAYER AND METHOD OF
MANUFACTURING THIN FILM
TRANSISTOR THEREBY

Customer No. 30827

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated April 9, 2004 (Paper No. 0331), please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper. This listing of claims replaces all prior versions and listings of claims in the application.

Remarks/Arguments begin on page 4 of this paper.